



**TO-251
(IPAK)**



**TO-252
(DPAK)**



Pin Definition:

1. Gate
2. Drain
3. Source

PRODUCT SUMMARY

BV_{CEO}	400V
BV_{CBO}	700V
I_C	2A
$V_{CE(SAT)}$	1.1V @ $I_C / I_B = 1A / 0.25A$

Features

- Build-in Free-wheeling Diode Makes Efficient Anti-saturation Operation
- No Need to Interest an hfe Value Because of Low Variable Storage-time Spread Even Though Comer Spirit Product.
- Low Base Drive Requirement
- Suitable for Half Bridge Light Ballast Application

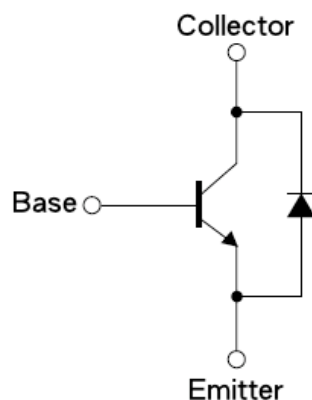
Structure

- Silicon Triple Diffused Type
- NPN Silicon Transistor with Diode

Ordering Information

Part No.	Package	Packing
TSC5302DCP RO	TO-252	2.5Kpcs / 13" Reel
TSC5302DCH C5	TO-251	70pcs / Tube

Block Diagram



Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V_{CBO}	700V	V
Collector-Emitter Voltage	V_{CEO}	400V	V
Emitter-Base Voltage	V_{EBO}	10	V
Collector Current	I_C	2	A
Collector Peak Current (tp < 5ms)	I_{CM}	4	A
Base Current	I_B	1	A
Base Peak Current (tp < 5ms)	I_{BM}	2	A
Total Dissipation @ Tc ≤ 25°C	TO-251	25	W
	TO-252	1.5	
Maximum Operating Junction Temperature	T_J	+150	°C
Storage Temperature Range	T_{STG}	-65 to +150	°C

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	$R\theta_{JC}$	6.25	$^{\circ}\text{C/W}$
Junction to Ambient Thermal Resistance	$R\theta_{JA}$	100	$^{\circ}\text{C/W}$

Electrical Specifications ($T_a = 25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Collector-Base Voltage	$I_C = 1\text{mA}, I_B = 0$	BV_{CBO}	700	--	--	V
Collector-Emitter Breakdown Voltage ^a	$I_C = 10\text{mA}, I_E = 0$	BV_{CEO}	400	--	--	V
Emitter-Base Breakdown Voltage	$I_E = 1\text{mA}, I_C = 0$	BV_{EBO}	10	--	--	V
Collector Cutoff Current	$V_{CB} = 700\text{V}, I_E = 0$	I_{CBO}	--	--	1	μA
Emitter Cutoff Current	$V_{EB} = 9\text{V}, I_C = 0$	I_{EBO}	--	--	1	μA
Collector-Emitter Saturation Voltage ^a	$I_C = 0.5\text{A}, I_B = 0.1\text{A}$	$V_{CE(SAT)1}$	--	--	0.5	V
	$I_C = 1\text{A}, I_B = 0.25\text{A}$	$V_{CE(SAT)2}$	--	--	1.1	
Base-Emitter Saturation Voltage ^a	$I_C = 0.5\text{A}, I_B = 0.1\text{A}$	$V_{BE(SAT)1}$	--	--	1.1	V
	$I_C = 1\text{A}, I_B = 0.25\text{A}$	$V_{BE(SAT)2}$	--	--	1.2	
DC Current Gain	$V_{CE} = 5\text{V}, I_C = 10\text{mA}$	$h_{FE} 1$	10	--	--	
	$V_{CE} = 5\text{V}, I_C = 400\text{mA}$	$h_{FE} 2$	10	--	30	
	$V_{CE} = 5\text{V}, I_C = 1\text{A}$	$h_{FE} 3$	5	--	--	
Turn On Time	$V_{CC} = 250\text{V}, I_C = 1\text{A}$	t_{ON}	--	0.15	0.3	μs
Storage Time	$I_{B1} = I_{B2} = 0.2\text{A}, t_p = 25\mu\text{s}$	t_{STG}	--	0.5	0.9	μs
Fall Time	Duty Cycle < 1%	t_f	--	0.2	0.4	μs
Diode						
Fall Time	$I_C = 1\text{A}$	t_F	--	--	800	μs
Forward Voltage Drop	$I_C = 1\text{A}$	V_f	--	--	1.4	V

Notes:

a. Pulsed duration = 300 μs , duty cycle $\leq 2\%$

Electrical Characteristics Curve ($T_a = 25^\circ\text{C}$, unless otherwise noted)

Figure 1. Static Characteristics

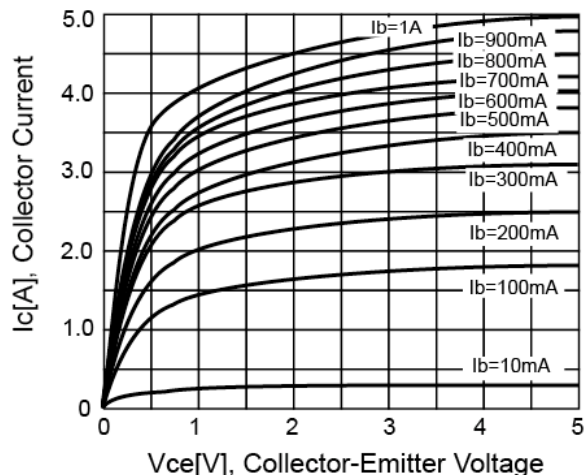


Figure 2. DC Current Gain

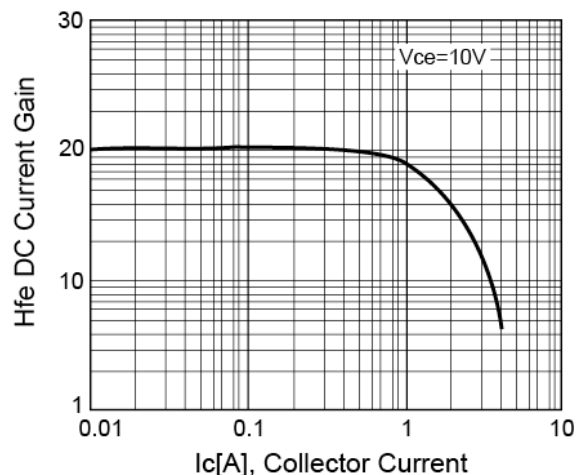


Figure 3. $V_{ce(sat)}$ v.s. $V_{be(sat)}$

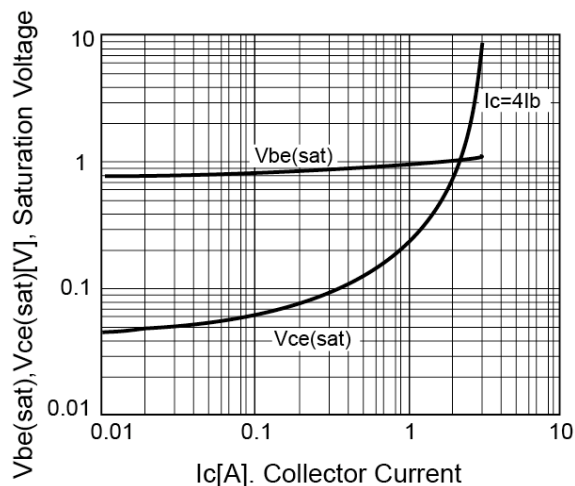
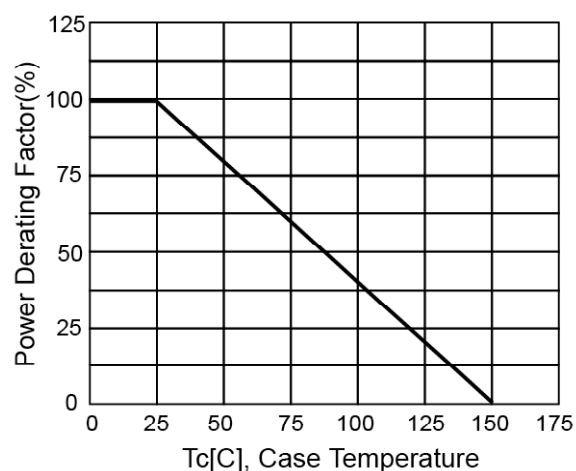
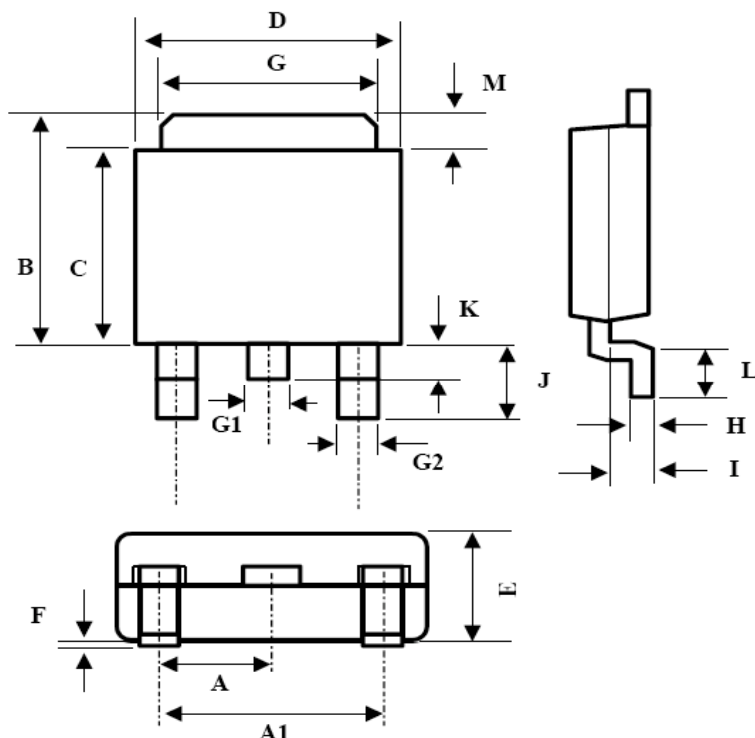


Figure 4. Power Derating

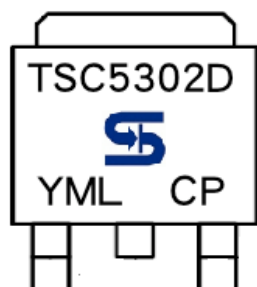


SOT-252 Mechanical Drawing



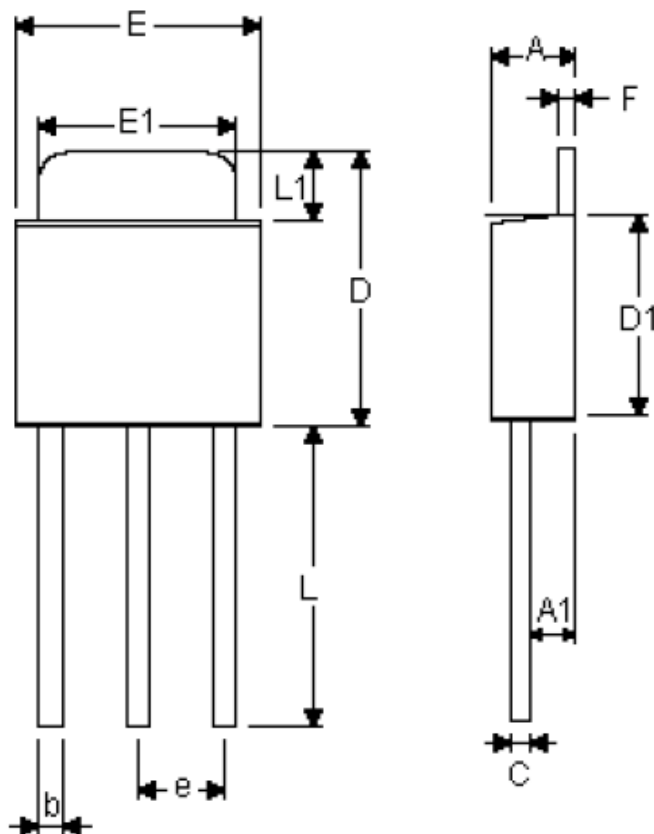
TO-252 DIMENSION				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.3BSC		0.09BSC	
A1	4.6BSC		0.18BSC	
B	6.80	7.20	0.268	0.283
C	5.40	5.60	0.213	0.220
D	6.40	6.65	0.252	0.262
E	2.20	2.40	0.087	0.094
F	0.00	0.20	0.000	0.008
G	5.20	5.40	0.205	0.213
G1	0.75	0.85	0.030	0.033
G2	0.55	0.65	0.022	0.026
H	0.35	0.65	0.014	0.026
I	0.90	1.50	0.035	0.059
J	2.20	2.80	0.087	0.110
K	0.50	1.10	0.020	0.043
L	0.90	1.50	0.035	0.059
M	1.30	1.70	0.051	0.67

Marking Diagram



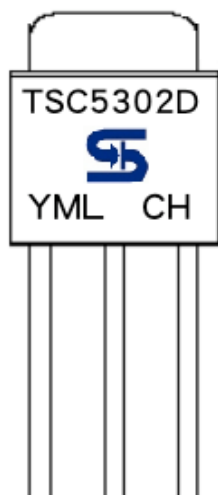
- Y** = Year Code
M = Month Code
 (A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)
L = Lot Code

SOT-251 Mechanical Drawing



DIM	TO-251 DIMENSION			
	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.20	2.40	0.087	0.094
A1	1.10	1.30	0.043	0.051
b	0.55	0.75	0.022	0.030
C	0.48	0.58	0.019	0.023
D	6.50	7.00	0.256	0.276
D1	5.50	5.70	0.217	0.224
E	6.40	6.60	0.252	0.260
E1	5.20	5.40	0.205	0.213
e	2.25	2.35	0.089	0.093
F	0.48	0.58	0.019	0.023
L	7.80	8.20	0.307	0.323
L1	1.00	1.30	0.039	0.051

Marking Diagram



- Y** = Year Code
- M** = Month Code
(**A**=Jan, **B**=Feb, **C**=Mar, **D**=Apr, **E**=May, **F**=Jun, **G**=Jul, **H**=Aug, **I**=Sep, **J**=Oct, **K**=Nov, **L**=Dec)
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